

## 1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



**Product data sheet** 

## 1. General description

Ultrafast, epitaxial rectifier diode in a SOD59 (TO-220AC) plastic package

## 2. Features and benefits

- · Fast switching
- Low thermal resistance
- · Soft recovery characteristic
- Low forward voltage drop
- · Low switching loss
- · High thermal cycling performance

## 3. Applications

- · Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_R$	reverse voltage	Square-wave; δ = 1.0		_	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 108 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	15	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le 108$ °C; Square-wave		-	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; Sinusoidal waveform; Fig. 4		-	-	130	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; Sinusoidal waveform		-	-	143	A
Static charact	eristics						,
$V_{F}$	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.17	1.38	V
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	50	60	ns

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# **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	А	anode	\ \ \ \ \ \ \ \	001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package		Version				
	Name	Description	Version				
BYT79-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59				

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## 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	Square-wave; δ = 1.0	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 108 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	A
I <sub>FRM</sub>	repetitive peak forward current	$δ = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \le 108 °C$ ; Square-wave	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; Sinusoidal waveform; Fig. 4	-	130	А
		t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; Sinusoidal waveform	-	143	A
T <sub>stg</sub>	storage temperature		-55	150	°C
T <sub>j</sub>	junction temperature		-	150	°C

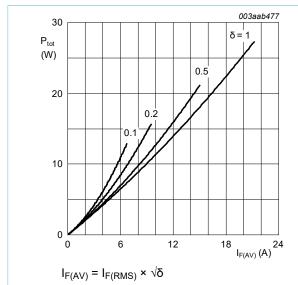


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

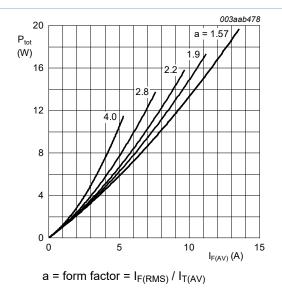


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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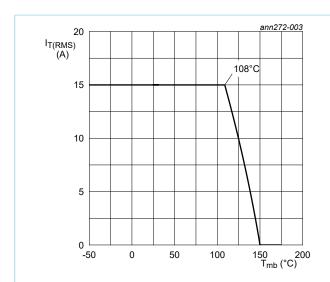


Fig. 3. RMS on-state current as a function of mounting base temperature; maximum values

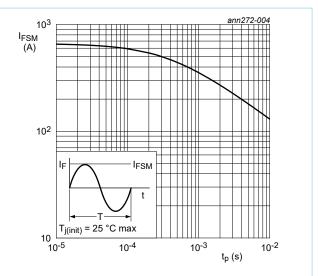


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air		-	60	-	K/W

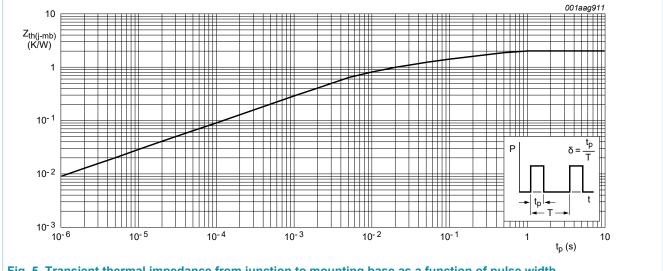


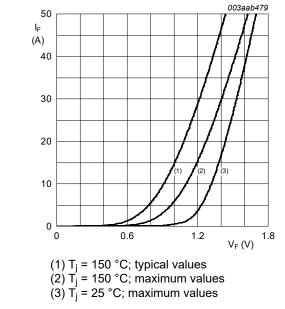
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

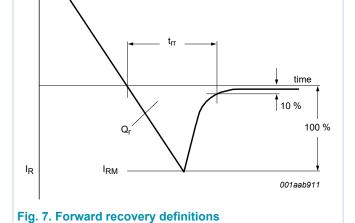
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## 9. Characteristics

#### **Table 6. Characteristics**

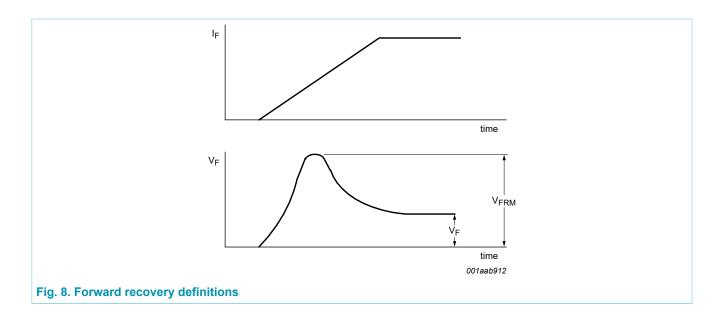
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.17	1.38	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	5	50	μΑ
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 100 °C	-	0.2	8.0	mA
Dynamic ch	naracteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/}\mu\text{s}$ ; Fig. 7	-	40	70	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; $\frac{\text{Fig. 7}}{}$	-	50	60	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; Fig. 7$	-	3	5.2	Α
$V_{FR}$	forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}; Fig. 8$	-	3.2	-	V





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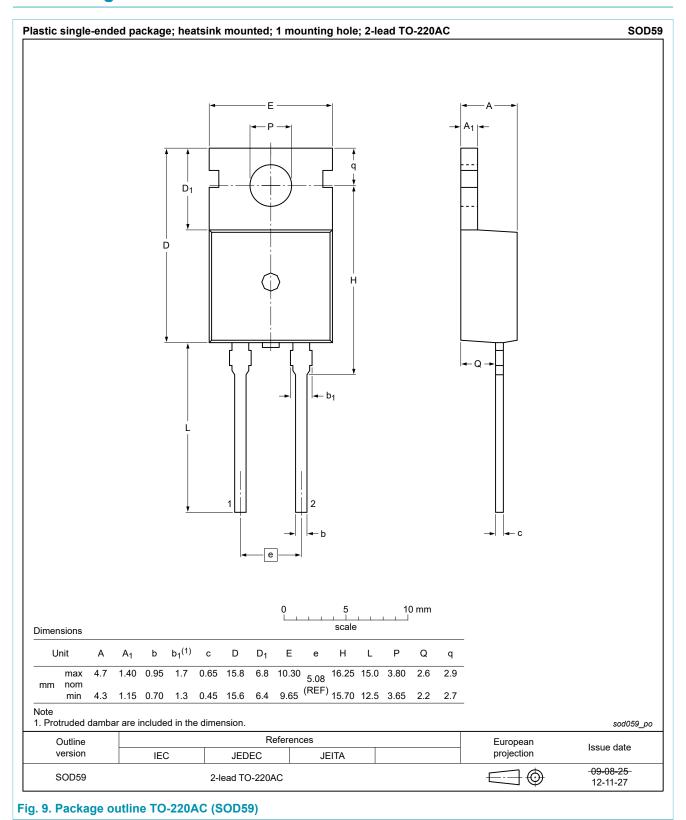
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**BYT79-600** 

## 10. Package outline



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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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